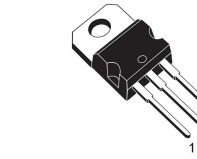
Silicon Controlled Rectifier series

1 Description

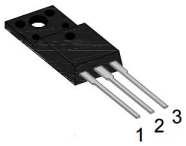
BT152 series of silicon controlled rectifiers, with high ability to withstand the shock loading of large current, provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on solid state

TO-220F provides insulation voltage rated at 2000V RMS from all three terminals to external heatsink. TO-220F series comply with UL standards (File ref: E252906).



V_{RRM}/V_{DRM} =600/800/1000
I_{GT} =≤25mA
$I_{T(RMS)}$ =20A

TO-220



TO-220F
Insulated

2 Features

- High current output up to 20A
- Low Peak on-state voltage drop
- High voltage
- High reliability

3 Applications

- relay
- Motorcycle
- power charger
- T-tools etc

4 Electrical Characteristics

4.1 Absolute Maximum Ratings （Tc=25℃,unless otherwise noted）

PARAMETER			SYMBOL	VALUE	UNIT
Repetitive peak off-state voltage (Tj=25℃)			V_{DRM}	600/800/1000	V
Repetitive peak reverse voltage (Tj=25℃)			V_{RRM}	600/800/1000	V
RMS on-state current	TO-220	(T_C=110℃)	$I_{T(RMS)}$	20	A
	TO-220F	(T_C=80℃)			
Non repetitive surge peak on-state current		tp=8.3ms	I_{TSM}	210	A
		tp=10ms		190	
I^2t value for fusing (tp=10ms)			I^2t	200	A
Repetitive rate of rise of on-state current ITM=20A IG=50mA dIG/dt 50mA/ms			$d_{IT/dt}$	50	A/us
Peak gate current			I_{GM}	4	A
Peak gate power			P_{GM}	5	W
Average gate power dissipation			$P_{G(AV)}$	1	W
Operating junction temperature range			T_J	- 40 ~ 125	℃
Storage junction temperature range			T_{STG}	- 40 ~ 150	℃

4.2 Thermal Characteristics

PARAMETER		SYMBOL	VALUE	UNIT
Thermal Resistance, Junction to Case-sink	TO-220	R_{thJC}	1.05	℃/W
	TO-220F		2.2	

4.3 Electrical Characteristics (Tc=25℃,unless otherwise noted)

SYMBOL	PARAMETER	Test Conditions		Min	Typ	Max	Unit
I_{GT}	Triggering gate current	V_D=12V R_L=33Ω		-	5	25	mA
V_{GT}	Triggering gate voltage			-	0.7	1.3	V
V_{GD}	Non-triggering gate voltage	V_D=V_{DRM} T_j=125℃ R_L=3.3KΩ		0.2	-	-	V
I_L	Latching Current	I_G=1.2I_{GT}		-	25	60	mA
I_H	Holding Current	I_T=500mA		-	15	30	mA
$dv_{/dt}$	Critical Rate of Rise of Off-state Voltage	V_D=2/3V_{DRM} Gate Open T_j=125℃		500	800	-	V/us
V_{TM}	Peak Forward On-State Voltage	I_{TM}=40A tp=380us		-	1.35	1.6	V
I_{DRM}	Maximum forward or reverse leakage current	V_D=V_{DRM} V_R=V_{RRM}	Tj=25℃	-	-	10	uA
I_{RRM}	Maximum reverse leakage current		Tj=125℃	-	-	1	mA

5 Typical characteristics diagrams

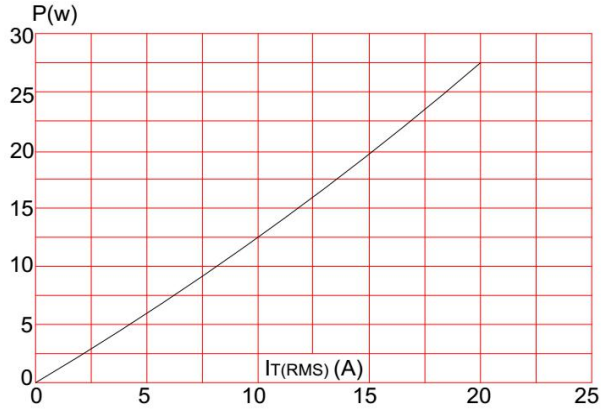


FIG.1: Maximum power dissipation versus RMS on-state current

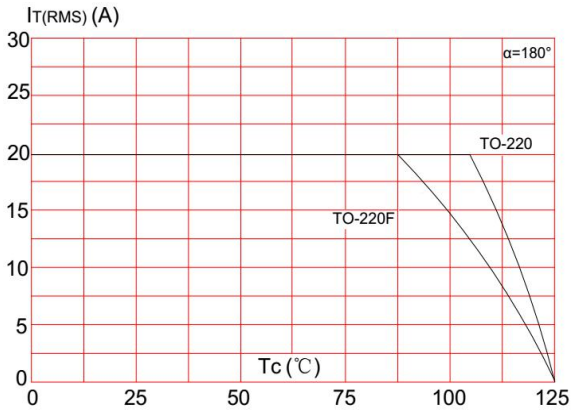


FIG.2: RMS on-state current versus case temperature

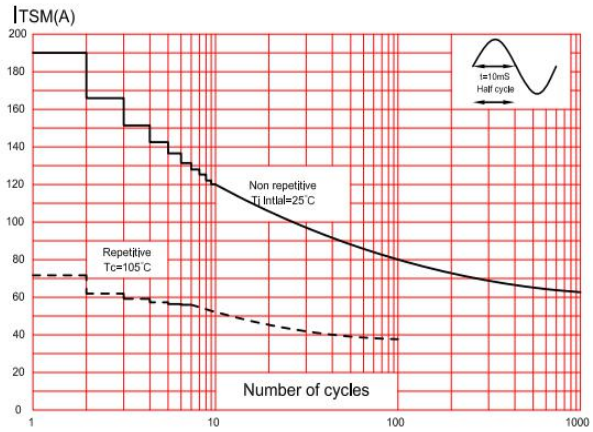


FIG.3: Surge peak on-state current versus number of cycles

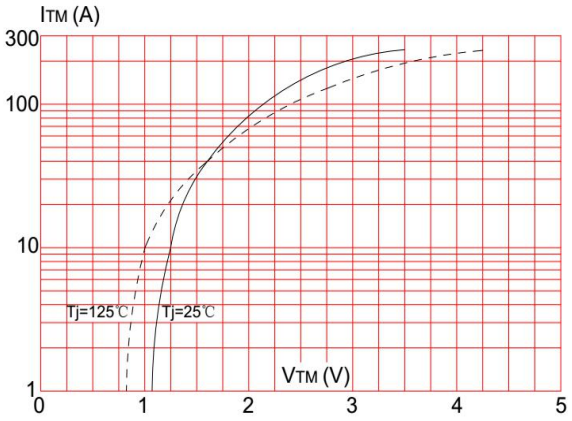


FIG.4: On-state characteristics (maximum values)

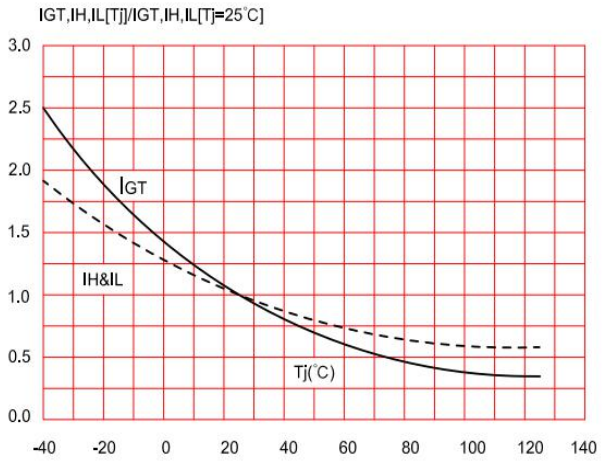
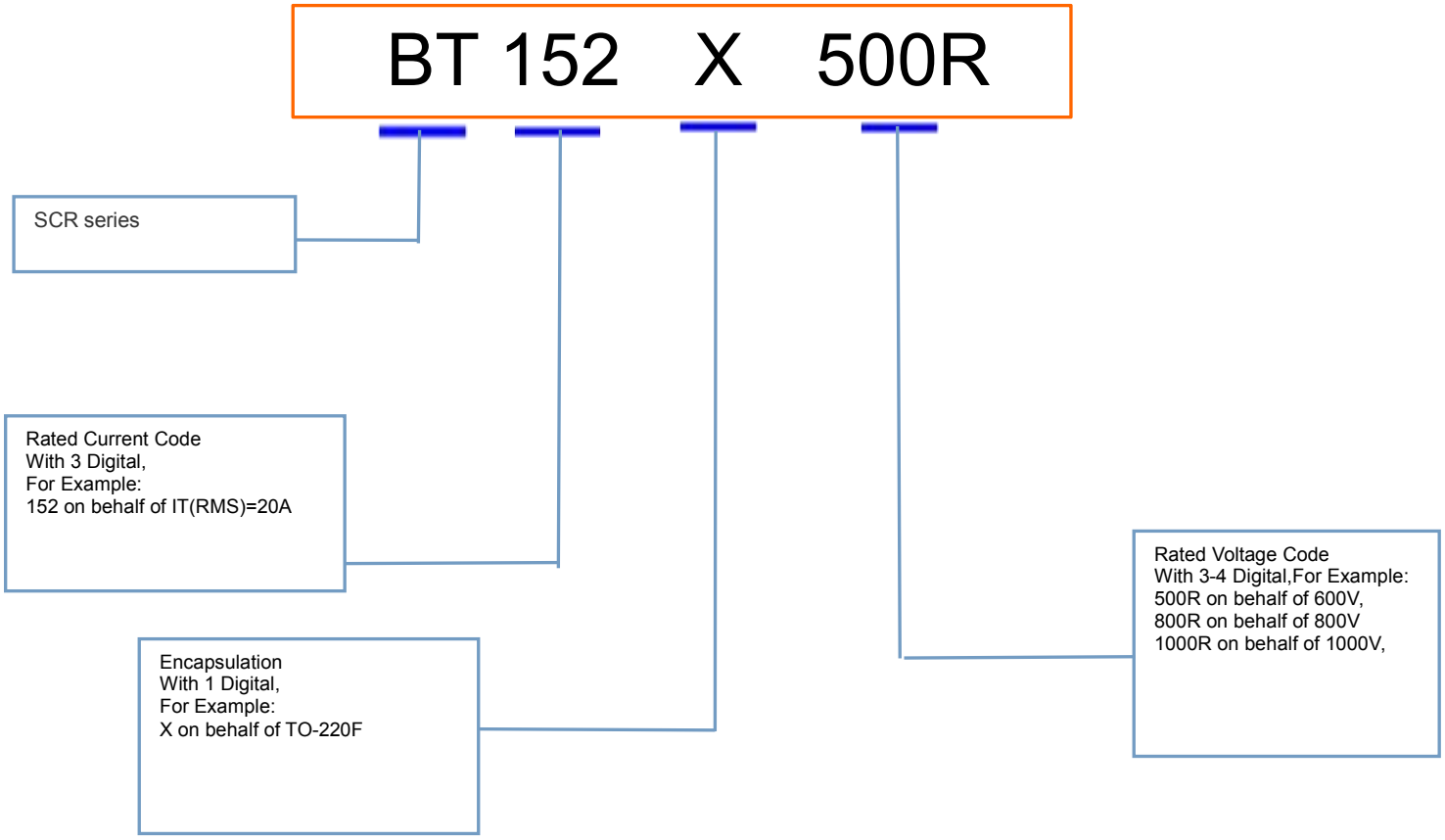


FIG.5: Relative variations of gate trigger current, holding current and latching current versus junction temperature

6 Product Names Rules

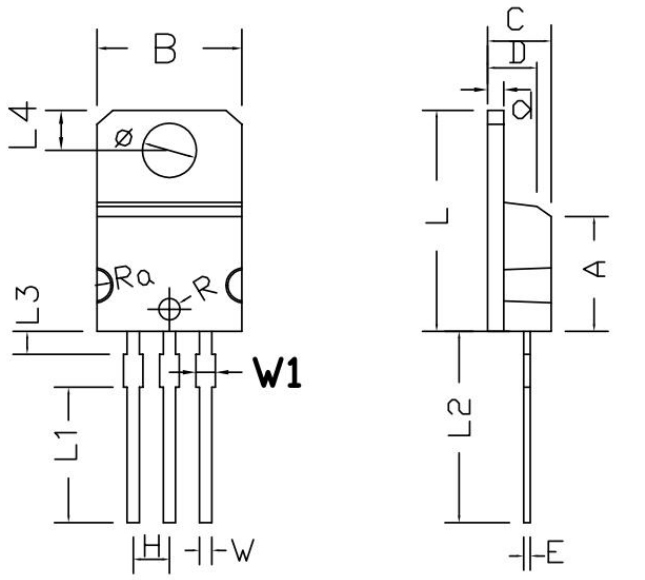


7 Product Specifications and Packaging Models

Product Model	Package Type	Mark Name	RoHS	Package	Quantity
BT152	TO-220	BT152	Pb-free	Tube	1000//box
BT152X	TO-220F	BT152X	Pb-free	Tube	1000//box

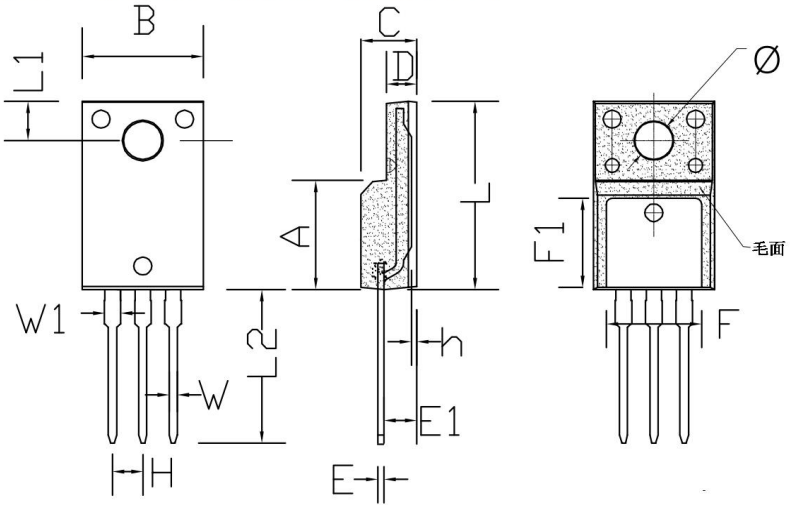
8 Dimensions

TO-220M PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	min.	max.	min.	max.
	MIN	MAX	MIN	MAX
A	8.03	8.05	0.316	0.317
B	10.13	10.23	0.399	0.403
C	4.42	4.52	0.174	0.178
D	3.42	3.52	0.135	0.139
E	0.44	0.46	0.017	0.018
L	15.25	15.45	0.601	0.609
H	2.52	2.56	0.099	0.101
W	0.85	0.87	0.033	0.034
Φ	3.60	3.90		
R	0.74	0.76	0.029	0.030
Ra	9.44	9.48	0.372	0.374
d	1.28	1.32	0.050	0.052
L1	9.4	9.6	0.370	0.378
L2	13.22	13.62	0.521	0.537
L3	1.52	1.72	0.060	0.068
L4	2.7	2.9	0.106	0.114
W1	1.32	1.42	0.052	0.056

TO-220F PACKAGE OUTLINE DIMENSIONS



Symbol	DimensionsIn Millimeters		DimensionsIn Inches	
	min.	max.	min.	max.
A	8.80	9.30	0.346	0.366
B	10.00	10.50	0.394	0.413
C	4.30	4.90	0.169	0.193
D	2.30	2.70	0.091	0.106
L	15.55	16.15	0.612	0.636
h	0.40	0.60	0.016	0.024
L1	3.15	3.55	0.124	0.140
L2	12.65	13.35	0.498	0.526
W	0.70	0.90	0.028	0.035
W1	1.15	1.55	0.045	0.061
H	2.54 TYP		0.100 TYP	
E	0.48	0.53	0.019	0.021
ϕ	2.90	3.40	0.114	0.134
E1	2.40	2.90	0.094	0.114
F	7.75	8.25	0.305	0.325
F1	7.35	7.85	0.289	0.309

9 Attentions

- Jiangsu Donghai Semiconductor Technology Co., Ltd. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of WXDH products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

10 Appendix

Revision history:

Date	REV.	Description	Page
2017.08.19	1.0	Original	